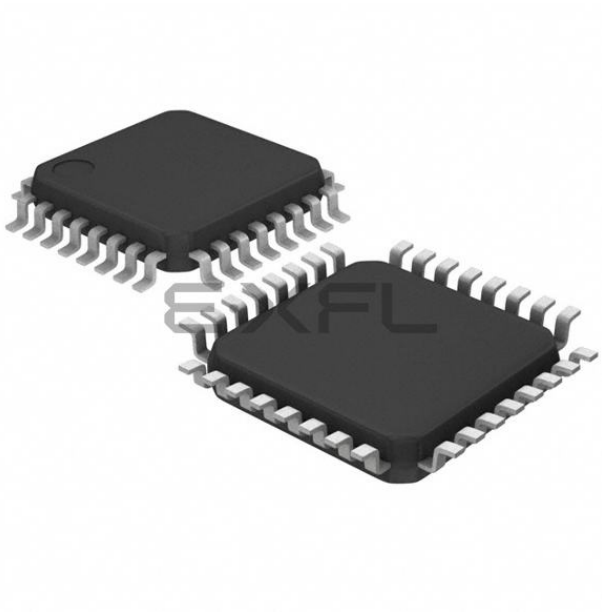

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	CIP-51 8051
Core Size	8-Bit
Speed	25MHz
Connectivity	EBI/EMI, I²C, SMBus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	24
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4.25K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 23x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-QFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm8sb20f64g-b-qfp32

Ordering Part Number	Flash Memory (kB)	RAM (Bytes)	Digital Port I/Os (Total)	ADC Channels	Comparator Inputs	Pb-free (RoHS Compliant)	Temperature Range	Package
EFM8SB20F16G-B-QFN24	16	4352	16	15	8	Yes	-40 to +85 C	QFN24

4. Electrical Specifications

4.1 Electrical Characteristics

All electrical parameters in all tables are specified under the conditions listed in Table 4.1 Recommended Operating Conditions on page 12, unless stated otherwise.

4.1.1 Recommended Operating Conditions

Table 4.1. Recommended Operating Conditions

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Operating Supply Voltage on VDD	V_{DD}		1.8	2.4	3.6	V
Minimum RAM Data Retention Voltage on VDD[1]	V_{RAM}	Not in Sleep Mode	—	1.4	—	V
		Sleep Mode	—	0.3	0.5	V
System Clock Frequency	f_{SYSCLK}		0	—	25	MHz
Operating Ambient Temperature	T_A		–40	—	85	°C

Note:
1. All voltages with respect to GND.

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Comparator 0 (CMP0) Supply Current	I_{CMP}	CPMD = 11	—	0.4	—	µA
		CPMD = 10	—	2.6	—	µA
		CPMD = 01	—	8.8	—	µA
		CPMD = 00	—	23	—	µA
Internal Fast-settling 1.65V ADC0 Reference, Always-on[8]	I_{VREFFS}		—	200	—	µA
On-chip Precision Reference	I_{VREFP}		—	15	—	µA
Temp sensor Supply Current	I_{TSENSE}		—	35	—	µA
Programmable Current Reference (IREF0) Supply Current[9]	I_{IREF}	Current Source, Either Power Mode, Any Output Code	—	10	—	µA
		Low Power Mode, Current Sink IREF0DAT = 000001	—	1	—	µA
		Low Power Mode, Current Sink IREF0DAT = 111111	—	11	—	µA
		High Current Mode, Current Sink IREF0DAT = 000001	—	12	—	µA
		High Current Mode, Current Sink IREF0DAT = 111111	—	81	—	µA

Note:

1. Based on device characterization data; Not production tested.
2. SYSCLK must be at least 32 kHz to enable debugging.
3. Digital Supply Current depends upon the particular code being executed. The values in this table are obtained with the CPU executing an “sjmp $” loop, which is the compiled form of a while(1) loop in C. One iteration requires 3 CPU clock cycles, and the flash memory is read on each cycle. The supply current will vary slightly based on the physical location of the sjmp instruction and the number of flash address lines that toggle as a result. In the worst case, current can increase by up to 30% if the sjmp loop straddles a 128-byte flash address boundary (e.g., 0x007F to 0x0080). Real-world code with larger loops and longer linear sequences will have few transitions across the 128-byte address boundaries.
4. Includes supply current from regulator and oscillator source (24.5 MHz high-frequency oscillator, 20 MHz low-power oscillator, or 32.768 kHz RTC oscillator).
5. IDD can be estimated for frequencies < 10 MHz by simply multiplying the frequency of interest by the frequency sensitivity number for that range, then adding an offset of 90 µA. When using these numbers to estimate I_{DD} for > 10 MHz, the estimate should be the current at 25 MHz minus the difference in current indicated by the frequency sensitivity number. For example: V_{DD} = 3.0 V; F = 20 MHz, I_{DD} = 4.1 mA – (25 MHz – 20 MHz) x 0.120 mA/MHz = 3.5 mA assuming the same oscillator setting.
6. Idle IDD can be estimated by taking the current at 25 MHz minus the difference in current indicated by the frequency sensitivity number. For example: V_{DD} = 3.0 V; F = 5 MHz, Idle I_{DD} = 2.5 mA – (25 MHz – 5 MHz) x 0.095 mA/MHz = 0.6 mA.
7. ADC0 always-on power excludes internal reference supply current.
8. The internal reference is enabled as-needed when operating the ADC in burst mode to save power.
9. IREF0 supply current only. Does not include current sourced or sunk from IREF0 output pin.

4.1.5 Power Management Timing

Table 4.5. Power Management Timing

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Idle Mode Wake-up Time	t_{IDLEWK}		2	—	3	SYSCLKs
Suspend Mode Wake-up Time	$t_{SUS-PENDWK}$	CLKDIV = 0x00 Precision Osc.	—	400	—	ns
		CLKDIV = 0x00 Low Power Osc.	—	1.3	—	µs
Sleep Mode Wake-up Time	$t_{SLEEPWK}$		—	2	—	µs

4.1.6 Internal Oscillators

Table 4.6. Internal Oscillators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
High Frequency Oscillator 0 (24.5 MHz)						
Oscillator Frequency	f_{HFOSC0}	Full Temperature and Supply Range	24	24.5	25	MHz
Low Power Oscillator (20 MHz)						
Oscillator Frequency	f_{LPOSC}	Full Temperature and Supply Range	18	20	22	MHz
RTC in Self-Oscillate Mode						
Oscillator Frequency	f_{LFOSC}	Bias Off	—	12 ± 5	—	kHz
		Bias On	—	25 ± 10	—	kHz

4.1.7 Crystal Oscillator

Table 4.7. Crystal Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal Frequency	f_{XTAL}		0.02	-	25	MHz

4.1.9 ADC

Table 4.9. ADC

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Resolution	N_{bits}			10		Bits
Throughput Rate	f_S		—	—	300	ksps
Tracking Time	t_{TRK}		1.5	—	—	µs
Power-On Time	t_{PWR}		1.5	—	—	µs
SAR Clock Frequency	f_{SAR}	High Speed Mode,	—	—	8.33	MHz
Conversion Time	T_{CNV}		13	—	—	Clocks
Sample/Hold Capacitor	C_{SAR}	Gain = 1	—	30	—	pF
		Gain = 0.5	—	28	—	pF
Input Pin Capacitance	C_{IN}		—	20	—	pF
Input Mux Impedance	R_{MUX}		—	5	—	kΩ
Voltage Reference Range	V_{REF}		1	—	V_{DD}	V
Input Voltage Range[1]	V_{IN}	Gain = 1	0	—	V_{REF}	V
		Gain = 0.5	0	—	2 x V_{REF}	V
Power Supply Rejection Ratio	$PSRR_{ADC}$	Internal High Speed VREF	—	67	—	dB
		External VREF	—	74	—	dB
DC Performance						
Integral Nonlinearity	INL		—	±0.5	±1	LSB
Differential Nonlinearity (Guaranteed Monotonic)	DNL		—	±0.5	±1	LSB
Offset Error	E_{OFF}	VREF = 1.65 V	–2	0	2	LSB
Offset Temperature Coefficient	TC_{OFF}		—	0.004	—	LSB/°C
Slope Error	E_M		—	±0.06	±0.24	%
Dynamic Performance 10 kHz Sine Wave Input 1dB below full scale, Max throughput						
Signal-to-Noise	SNR		54	58	—	dB
Signal-to-Noise Plus Distortion	SNDR		54	58	—	dB
Total Harmonic Distortion (Up to 5th Harmonic)	THD		—	-73	—	dB
Spurious-Free Dynamic Range	SFDR		—	75	—	dB

Note:
1. Absolute input pin voltage is limited by the V_{DD} supply.

4.1.10 Voltage References

Table 4.10. Voltage References

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Internal Fast Settling Reference						
Output Voltage	V_{REFFS}		1.60	1.65	1.70	V
Temperature Coefficient	TC_{REFFS}		—	50	—	ppm/°C
Turn-on Time	t_{VREFFS}		—	—	1.5	µs
Power Supply Rejection	$PSRR_{REFFS}$		—	400	—	ppm/V
On-chip Precision Reference						
Output Voltage	V_{REFP}		1.645	1.68	1.715	V
Turn-on Time, settling to 0.5 LSB	t_{VREFP}	4.7 µF tantalum + 0.1 µF ceramic bypass on VREF pin	—	15	—	ms
		0.1 µF ceramic bypass on VREF pin	—	300	—	µs
		No bypass on VREF pin	—	25	—	µs
Load Regulation	LR_{VREFP}	Load = 0 to 200 µA to GND	—	400	—	µV / µA
Short-circuit current	ISC_{VREFP}		—	3.5	—	mA
Power Supply Rejection	$PSRR_{VREFP}$		—	140	—	ppm/V
External Reference						
Input Voltage	V_{EXTREF}		1	—	V_{DD}	V
Input Current	I_{EXTREF}	Sample Rate = 300 ksps; VREF = 3.0 V	—	5.25	—	µA

4.1.11 Temperature Sensor

Table 4.11. Temperature Sensor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Offset	V_{OFF}	T_A = 0 °C	—	940	—	mV
Offset Error[1]	E_{OFF}	T_A = 0 °C	—	18	—	mV
Slope	M		—	3.40	—	mV/°C
Slope Error[1]	E_M		—	40	—	µV/°C
Linearity			—	±1	—	°C
Turn-on Time	t_{PWR}		—	1.8	—	µs

Note:
1. Represents one standard deviation from the mean.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Negative Hysteresis Mode 3 (CPMD = 11)	HYS_{CP-}	CPHYN = 00	—	-1.5	—	mV
		CPHYN = 01	—	–4	—	mV
		CPHYN = 10	—	–8	—	mV
		CPHYN = 11	—	–16	—	mV
Input Range (CP+ or CP–)	V_{IN}		-0.25	—	V_{DD}+0.25	V
Input Pin Capacitance	C_{CP}		—	12	—	pF
Common-Mode Rejection Ratio	$CMRR_{CP}$		—	70	—	dB
Power Supply Rejection Ratio	$PSRR_{CP}$		—	72	—	dB
Input Offset Voltage	V_{OFF}	T_A = 25 °C	-10	0	10	mV
Input Offset Tempco	TC_{OFF}		—	3.5	—	µV/°C

4.1.13 Programmable Current Reference (IREF0)

Table 4.13. Programmable Current Reference (IREF0)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Performance						
Resolution	N_{bits}			6		bits
Output Compliance Range	V_{IOUT}	Low Power Mode, Source	0	—	V_{DD} – 0.4	V
		High Current Mode, Source	0	—	V_{DD} – 0.8	V
		Low Power Mode, Sink	0.3	—	V_{DD}	V
		High Current Mode, Sink	0.8	—	V_{DD}	V
Integral Nonlinearity	INL		—	<±0.2	±1.0	LSB
Differential Nonlinearity	DNL		—	<±0.2	±1.0	LSB
Offset Error	E_{OFF}		—	<±0.1	±0.5	LSB
Full Scale Error	E_{FS}	Low Power Mode, Source	—	—	±5	%
		High Current Mode, Source	—	—	±6	%
		Low Power Mode, Sink	—	—	±8	%
		High Current Mode, Sink	—	—	±8	%
Absolute Current Error	E_{ABS}	Low Power Mode Sourcing 20 µA	—	<±1	±3	%
Dynamic Performance						
Output Settling Time to 1/2 LSB	t_{SETTLE}		—	300	—	ns
Startup Time	t_{PWR}		—	1	—	µs

Note:
1. The PCA block may be used to improve IREF0 resolution by PWMing the two LSBs.

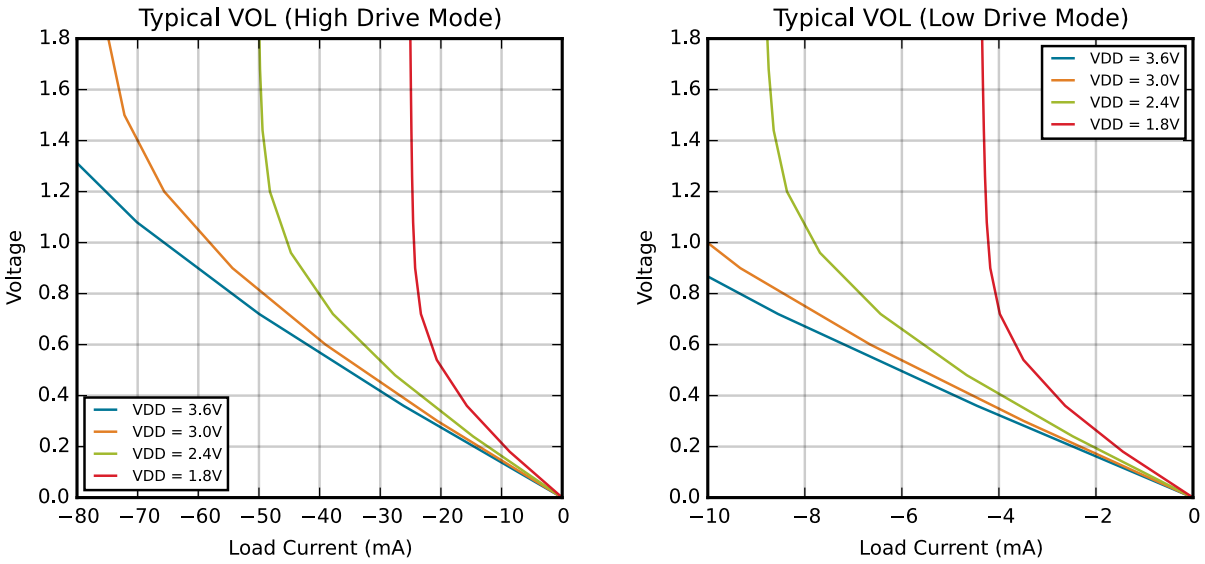


Figure 4.3. Typical V_{OL} Curves

5.3 Other Connections

Other components or connections may be required to meet the system-level requirements. Application note, "AN203: 8-bit MCU Printed Circuit Board Design Notes", contains detailed information on these connections. Application Notes can be accessed on the Silicon Labs website (www.silabs.com/8bit-appnotes).

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
5	N/C	No Connection			
6	RSTb / C2CK	Active-low Reset / C2 Debug Clock			
7	P2.7 / C2D	Multifunction I/O / C2 Debug Data			
8	P2.6	Multifunction I/O	Yes	EMIF_WRb	ADC0.22 CMP0P.11 CMP1P.11
9	XTAL4	RTC Crystal			XTAL4
10	XTAL3	RTC Crystal			XTAL3
11	P2.5	Multifunction I/O	Yes	EMIF_RDb	ADC0.21 CMP0N.10 CMP1N.10
12	P2.4	Multifunction I/O	Yes	EMIF_ALE	ADC0.20 CMP0P.10 CMP1P.10
13	P2.3	Multifunction I/O	Yes	EMIF_A11	ADC0.19 CMP0N.9 CMP1N.9
14	P2.2	Multifunction I/O	Yes	EMIF_A10	ADC0.18 CMP0P.9 CMP1P.9
15	P2.1	Multifunction I/O	Yes	EMIF_A9	ADC0.17 CMP0N.8 CMP1N.8
16	P2.0	Multifunction I/O	Yes	EMIF_A8	ADC0.16 CMP0P.8 CMP1P.8
17	P1.7	Multifunction I/O	Yes	P1MAT.7 EMIF_AD7	ADC0.15 CMP0N.7 CMP1N.7
18	P1.6	Multifunction I/O	Yes	P1MAT.6 EMIF_AD6	ADC0.14 CMP0P.7 CMP1P.7

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
19	P1.5	Multifunction I/O	Yes	P1MAT.5 EMIF_AD5	ADC0.13 CMP0N.6 CMP1N.6
20	P1.4	Multifunction I/O	Yes	P1MAT.4 EMIF_AD4	ADC0.12 CMP0P.6 CMP1P.6
21	P1.3	Multifunction I/O	Yes	P1MAT.3 SPI1_NSS EMIF_AD3	ADC0.11 CMP0N.5 CMP1N.5
22	P1.2	Multifunction I/O	Yes	P1MAT.2 SPI1_MOSI EMIF_AD2	ADC0.10 CMP0P.5 CMP1P.5
23	P1.1	Multifunction I/O	Yes	P1MAT.1 SPI1_MISO EMIF_AD1	ADC0.9 CMP0N.4 CMP1N.4
24	P1.0	Multifunction I/O	Yes	P1MAT.0 SPI1_SCK EMIF_AD0	ADC0.8 CMP0P.4 CMP1P.4
25	P0.7	Multifunction I/O	Yes	P0MAT.7 INT0.7 INT1.7	ADC0.7 IREF0 CMP0N.3 CMP1N.3
26	P0.6	Multifunction I/O	Yes	P0MAT.6 CNVSTR INT0.6 INT1.6	ADC0.6 CMP0P.3 CMP1P.3
27	P0.5	Multifunction I/O	Yes	P0MAT.5 INT0.5 INT1.5	ADC0.5 CMP0N.2 CMP1N.2
28	P0.4	Multifunction I/O	Yes	P0MAT.4 INT0.4 INT1.4	ADC0.4 CMP0P.2 CMP1P.2
29	P0.3	Multifunction I/O	Yes	P0MAT.3 EXTCLK INT0.3 INT1.3	ADC0.3 XTAL2 CMP0N.1 CMP1N.1

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
6	RSTb / C2CK	Active-low Reset / C2 Debug Clock			
7	P2.7 / C2D	Multifunction I/O / C2 Debug Data			
8	XTAL4	RTC Crystal			XTAL4
9	XTAL3	RTC Crystal			XTAL3
10	P1.6	Multifunction I/O	Yes		ADC0.14 CMP0P.7 CMP1P.7
11	P1.5	Multifunction I/O	Yes	P1MAT.5	ADC0.13 CMP0N.6 CMP1N.6
12	P1.4	Multifunction I/O	Yes	P1MAT.4	ADC0.12 CMP0P.6 CMP1P.6
13	P1.3	Multifunction I/O	Yes	P1MAT.3 SPI1_NSS	ADC0.11 CMP0N.5 CMP1N.5
14	P1.2	Multifunction I/O	Yes	P1MAT.2 SPI1_MOSI	ADC0.10 CMP0P.5 CMP1P.5
15	P1.1	Multifunction I/O	Yes	P1MAT.1 SPI1_MISO	ADC0.9 CMP0N.4 CMP1N.4
16	P1.0	Multifunction I/O	Yes	P1MAT.0 SPI1_SCK	ADC0.8 CMP0P.4 CMP1P.4
17	P0.7	Multifunction I/O	Yes	P0MAT.7 INT0.7 INT1.7	ADC0.7 IREF0 CMP0N.3 CMP1N.3
18	P0.6	Multifunction I/O	Yes	P0MAT.6 CNVSTR INT0.6 INT1.6	ADC0.6 CMP0P.3 CMP1P.3

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
8	P2.6	Multifunction I/O	Yes	EMIF_WRb	ADC0.22 CMP0P.11 CMP1P.11
9	XTAL4	RTC Crystal			XTAL4
10	XTAL3	RTC Crystal			XTAL3
11	P2.5	Multifunction I/O	Yes	EMIF_RDb	ADC0.21 CMP0N.10 CMP1N.10
12	P2.4	Multifunction I/O	Yes	EMIF_ALE	ADC0.20 CMP0P.10 CMP1P.10
13	P2.3	Multifunction I/O	Yes	EMIF_A11	ADC0.19 CMP0N.9 CMP1N.9
14	P2.2	Multifunction I/O	Yes	EMIF_A10	ADC0.18 CMP0P.9 CMP1P.9
15	P2.1	Multifunction I/O	Yes	EMIF_A9	ADC0.17 CMP0N.8 CMP1N.8
16	P2.0	Multifunction I/O	Yes	EMIF_A8	ADC0.16 CMP0P.8 CMP1P.8
17	P1.7	Multifunction I/O	Yes	P1MAT.7 EMIF_AD7	ADC0.15 CMP0N.7 CMP1N.7
18	P1.6	Multifunction I/O	Yes	P1MAT.6 EMIF_AD6	ADC0.14 CMP0P.7 CMP1P.7
19	P1.5	Multifunction I/O	Yes	P1MAT.5 EMIF_AD5	ADC0.13 CMP0N.6 CMP1N.6
20	P1.4	Multifunction I/O	Yes	P1MAT.4 EMIF_AD4	ADC0.12 CMP0P.6 CMP1P.6

7. QFN32 Package Specifications

7.1 QFN32 Package Dimensions

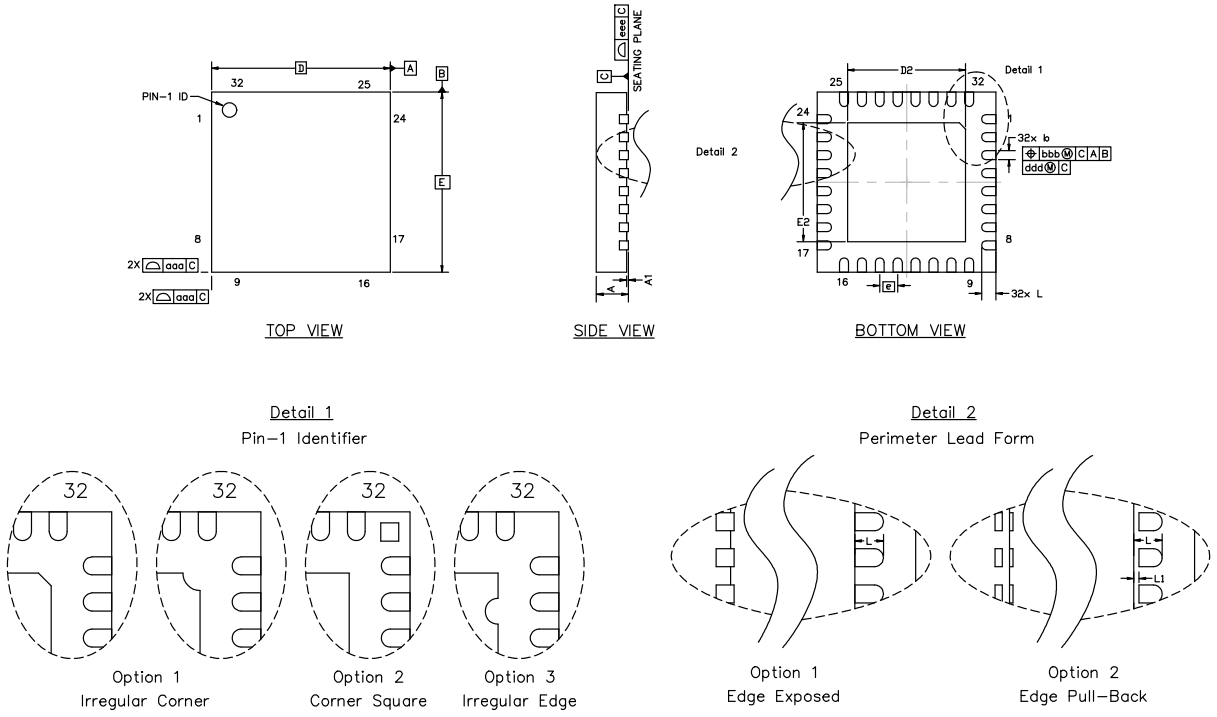


Figure 7.1. QFN32 Package Drawing

Table 7.1. QFN32 Package Dimensions

Dimension	Min	Typ	Max
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
b	0.18	0.25	0.30
D		5.00 BSC	
D2	3.20	3.30	3.40
e		0.50 BSC	
E		5.00 BSC	
E2	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.00	—	0.15
aaa	—	—	0.15

Dimension	Min	Typ	Max
bbb	—	—	0.10
ddd	—	—	0.05
eee	—	—	0.08

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This drawing conforms to JEDEC Solid State Outline MO-220, variation VHHD except for custom features D2, E2, and L which are toleranced per supplier designation.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

7.3 QFN32 Package Marking

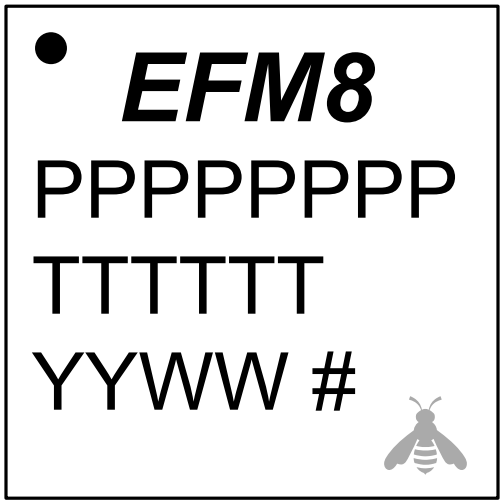


Figure 7.3. QFN32 Package Marking

The package marking consists of:

- PPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.
- # – The device revision (A, B, etc.).

Dimension	Min	Typ	Max
bbb	—	—	0.10
ddd	—	—	0.05
eee	—	—	0.08
Z	—	0.24	—
Y	—	0.18	—

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This drawing conforms to JEDEC Solid State Outline MO-220, variation WGGD except for custom features D2, E2, Z, Y, and L which are toleranced per supplier designation.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

Dimension	Min	Max

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
5. The stencil thickness should be 0.125 mm (5 mils).
6. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads.
7. A 2 x 2 array of 1.10 mm x 1.10 mm openings on 1.30 mm pitch should be used for the center ground pad.
8. A No-Clean, Type-3 solder paste is recommended.
9. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

8.3 QFN24 Package Marking

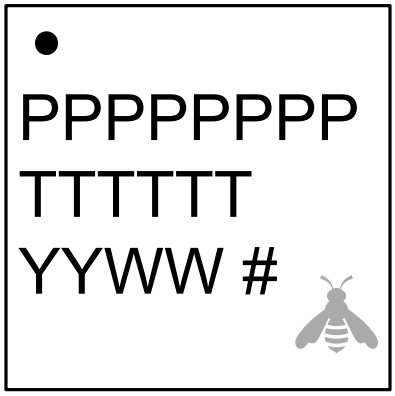


Figure 8.3. QFN24 Package Marking

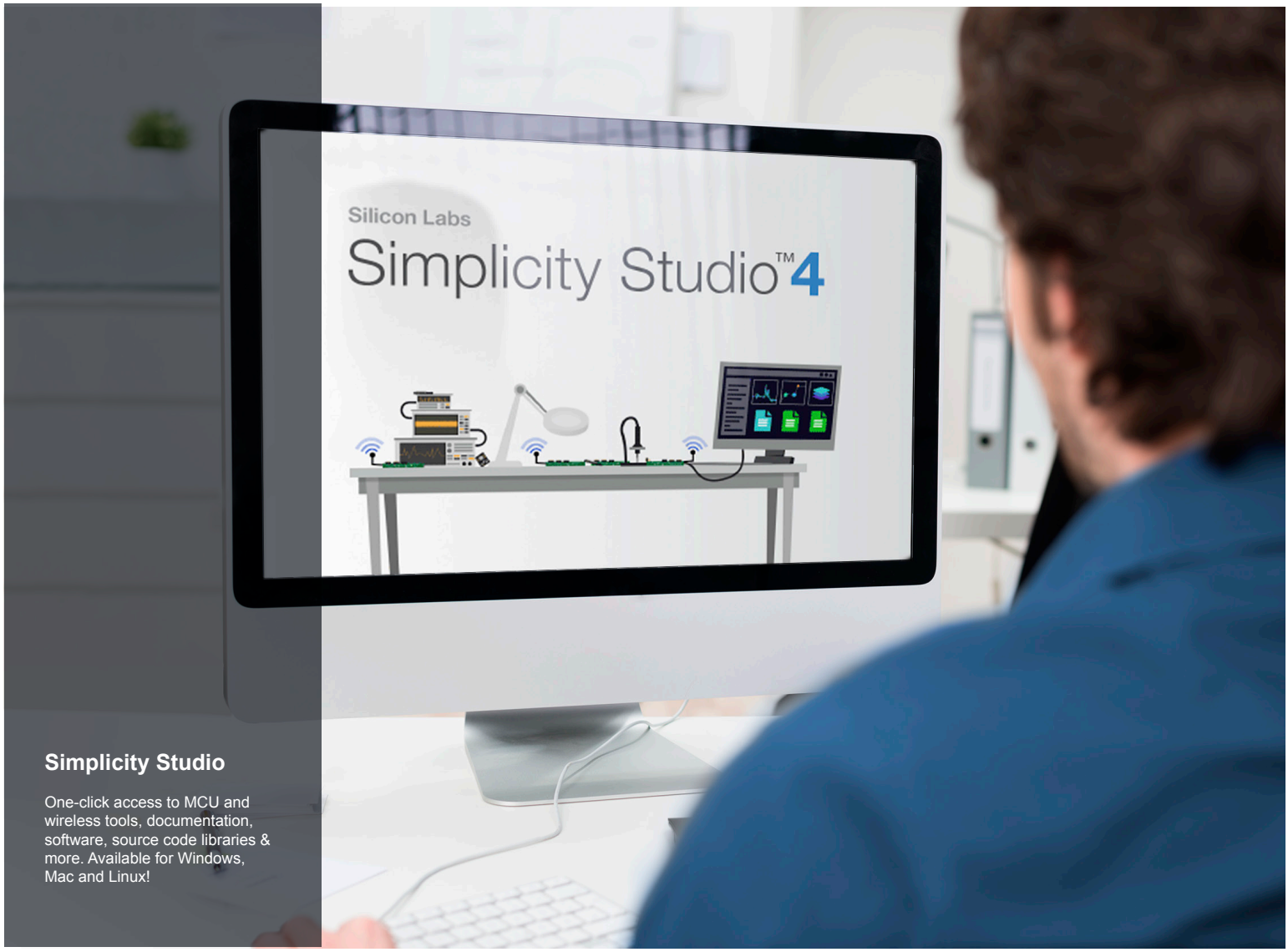
The package marking consists of:

- PPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.
- # – The device revision (A, B, etc.).

Dimension	Min	Typ	Max
bbb		0.20	
ccc		0.10	
ddd		0.20	
theta	0°	3.5°	7°

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This drawing conforms to JEDEC outline MS-026, variation BBA.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.



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